

## PART ONE: General description

Lithography1

*Process name*

UL3\_001

*Process Code*

04/24/00

*Last Update*

Udo Lang

*Author*

lang@ee

*Contact Information (Email)*

AZ1512 - resist thickness approx - 1 mic.

*General description of process*

## PART TWO: Details

### Cleaning

Nano-strip

10

*Time (min)*

BOE

*Time (min)*

### Rinse and Dry

### Resist Coating

P-10

*Primer*

*Speed1 (RPM)*

*Time(sec)*

*Speed2 (RPM)*

*Time(sec)*

HMDS

AZ 1512

*Resist*

700

*Speed1 (RPM)*

5

*Time(sec)*

3000

*Speed2 (RPM)*

30

*Time(sec)*

PreBake

Oven

80

*T (°C)*

30

*Time(min)*

Exposure

3" Aligner

14

*Time(sec)*

Develop

AZ351:H2O (1:4)

*Developer*

120

*Time(sec)*

PostBake

Oven

120

*T (°C)*

30

*Time(min)*

### Rinse and Dry

### **PART THREE: General Comments**

No problems encountered if enough PR is spun on. Otherwise or if Pr sat too long on the wafer then streaks.

Alternatives:

Spinning on of Primer P-10 instead of HMDS oven

Pre bake and Post bake on hotplate

For 4" aligner exposure 15 sec